CY62126DV30 MoBL®

1-Mbit (64K x 16) Static RAM

Features

- **Very high speed**
  - **55 ns**
- **Temperature Ranges**
  - **Industrial: –40°C to 85°C**
  - **Automotive: –40°C to 125°C**
- **Wide voltage range**
  - **2.2V - 3.6V**
- **Pin compatible with CY62126BV**
- **Ultra-low active power**
  - **Typical active current: 0.85 mA @ f = 1 MHz**
  - **Typical active current: 5 mA @ f = f_{Max} (55 ns speed)**
- **Ultra-low standby power**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **Available in Pb-free and non Pb-free 48-ball VFBGA and 44-pin TSOP Type II packages**

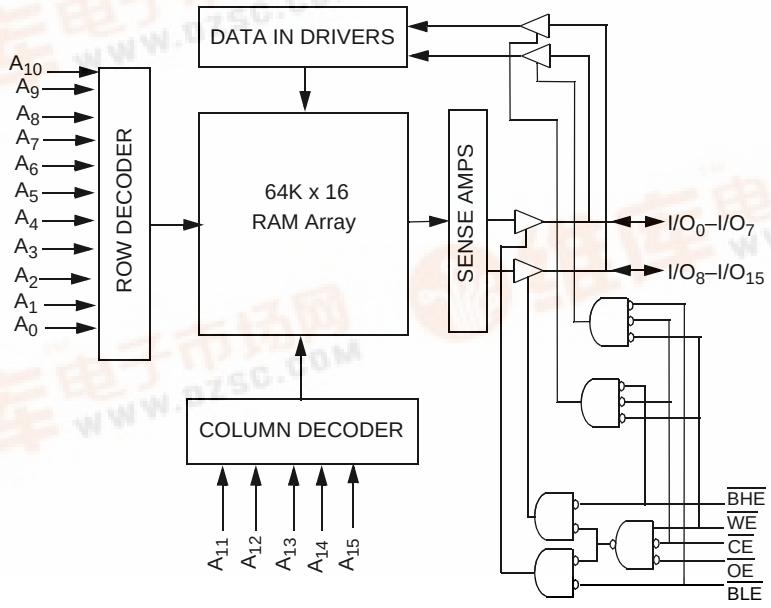
Functional Description[1]

The CY62126DV30 is a high-performance CMOS static RAM organized as 64K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption by 90% when addresses are not toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected ($\overline{CE}$ HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH) or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{15}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{15}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

Logic Block Diagram



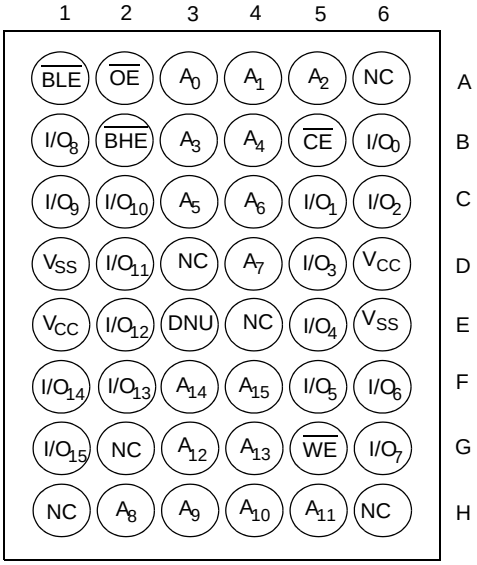
Note:
1. For best-practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Product Portfolio

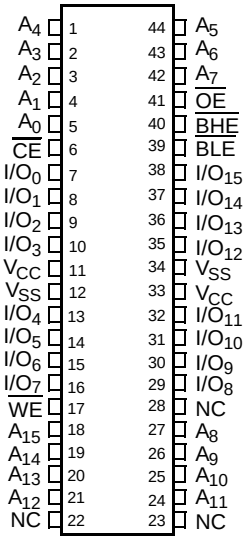
Product	Range	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
						Operating, I_{CC} (mA)				Standby, I_{SB2} (µA)	
						f = 1 MHz		f = f_{Max}			
		Min.	Typ.	Max.		Typ.[2]	Max.	Typ.[2]	Max.	Typ.[2]	Max.
CY62126DV30L	Automotive	2.2	3.0	3.6	55	0.85	1.5	5	10	1.5	15
CY62126DV30LL	Industrial				55	0.85	1.5	5	10	1.5	4

Pin Configurations[3, 4]

48-ball VFBGA
Top View



TSOP II (Forward)
Top View



Notes:
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25°C$.
3. NC pins are not connected to the die.
4. E3 (DNU) can be left as NC or V_{SS} to ensure proper operation. (Expansion Pins on FBGA Package: E4 - 2M, D3 - 4M, H1 - 8M, G2 - 16M, H6 - 32M).

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage to Ground Potential.....–0.3 to 3.9V

DC Voltage Applied to Outputs in High-Z State[6] .....–0.3V to V_{CC} + 0.3V

DC Input Voltage[6] .....–0.3V to V_{CC} + 0.3V

Output Current into Outputs (LOW).....20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current .....> 200 mA

Operating Range

Range	Ambient Temperature (T_A)	V_{CC}[7]
Industrial	–40°C to +85°C	2.2V to 3.6V
Automotive	–40°C to +125°C	2.2V to 3.6V

DC Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions				CY62126DV30-55 Min.	Typ.[5]	Max.	Unit
V_{OH}	Output HIGH Voltage	2.2V ≤ V_{CC} ≤ 2.7V	I_{OH} = –0.1 mA			2.0			V
		2.7V ≤ V_{CC} ≤ 3.6V	I_{OH} = –1.0 mA			2.4			
V_{OL}	Output LOW Voltage	2.2V ≤ V_{CC} ≤ 2.7V	I_{OL} = 0.1 mA					0.4	V
		2.7V ≤ V_{CC} ≤ 3.6V	I_{OL} = 2.1 mA					0.4	
V_{IH}	Input HIGH Voltage	2.2V ≤ V_{CC} ≤ 2.7V				1.8		V_{CC} + 0.3	V
		2.7V ≤ V_{CC} ≤ 3.6V				2.2		V_{CC} + 0.3	
V_{IL}	Input LOW Voltage	2.2V ≤ V_{CC} ≤ 2.7V				–0.3		0.6	V
		2.7V ≤ V_{CC} ≤ 3.6V				–0.3		0.8	
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}			Ind'l	–1		+1	µA
					Auto	–4		+4	
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled			Ind'l	–1		+1	µA
					Auto	–4		+4	
I_{CC}	V_{CC} Operating Supply Current	f = f_{Max} = 1/t_{RC}	V_{CC} = 3.6V, I_{OUT} = 0 mA, CMOS level				5	10	mA
		f = 1 MHz					0.85	1.5	
I_{SB1}	Automatic CE Power-down Current—CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V, V_{IN} ≤ 0.2V, f = f_{Max} (Address and Data Only), f = 0 ($\overline{OE}$, $\overline{WE}$, $\overline{BHE}$ and $\overline{BLE}$)		L	Ind'l		1.5	5	µA
					Auto		1.5	15	
				LL			1.5	4	
I_{SB2}	Automatic CE Power-down Current—CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.6V		L	Ind'l		1.5	5	µA
					Auto		1.5	15	
				LL			1.5	4	

Notes:
5. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ)}$, T_A = 25°C.
6. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns., $V_{IH(max.)}$ = V_{CC} + 0.75V for pulse durations less than 20 ns.
7. Full device operation requires linear ramp of V_{CC} from 0V to $V_{CC(min)}$ & V_{CC} must be stable at $V_{CC(min)}$ for 500 µs.

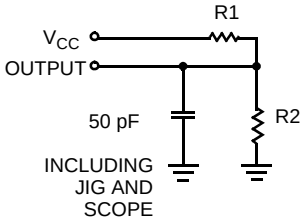
Capacitance[8]

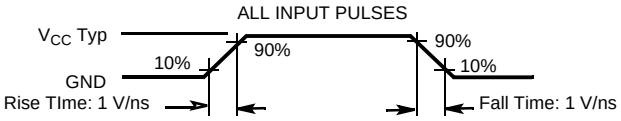
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[8]

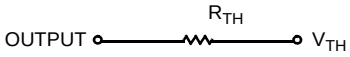
Parameter	Description	Test Conditions	TSOP	VFBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, 2-layer printed circuit board	55	76	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		12	11	°C/W

AC Test Loads and Waveforms





Equivalent to: THEVENIN EQUIVALENT

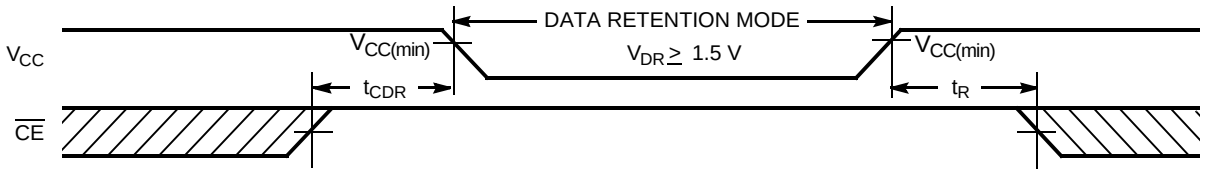


Parameters	2.5V	3.0V	Unit
R1	16600	1103	Ohms
R2	15400	1554	Ohms
R_{TH}	8000	645	Ohms
V_{TH}	1.2	1.75	Volts

Data Retention Characteristics

Parameter	Description	Conditions			Min.	Typ[2]	Max.	Unit
V_{DR}	V_{CC} for Data Retention				1.5			V
I_{CCDR}	Data Retention Current	V_{CC}=1.5V, $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	L	Ind'l			4	µA
			L	Auto			10	
			LL	Ind'l			3	
t_{CDR}[8]	Chip Deselect to Data Retention Time				0			ns
t_R[9]	Operation Recovery Time				100			µs

Data Retention Waveform



Notes:
8. Tested initially and after any design or proces changes that may affect these parameters.
9. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)}$ >100 µs.

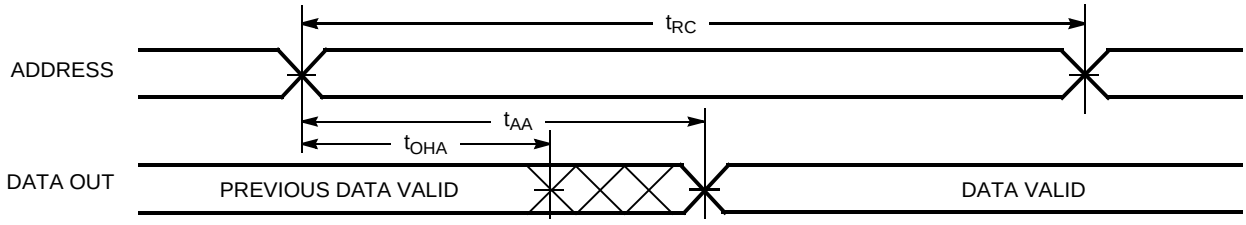
Switching Characteristics (Over the Operating Range)[10]

Parameter	Description	CY62126DV30-55		Unit
		Min.	Max.	
Read Cycle				
t_{RC}	Read Cycle Time	55		ns
t_{AA}	Address to Data Valid		55	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		55	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[11]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[11, 12]		20	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[11]	10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[11, 12]		20	ns
t_{PU}	$\overline{CE}$ LOW to Power-up	0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-down		55	ns
t_{DBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Data Valid		25	ns
t_{LZBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Low Z[11]	5		ns
t_{HZBE}	$\overline{BLE}$/$\overline{BHE}$ HIGH to High-Z[11, 12]		20	ns
Write Cycle[13]				
t_{WC}	Write Cycle Time	55		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	40		ns
t_{AW}	Address Set-up to Write End	40		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	40		ns
t_{BW}	$\overline{BLE}$/$\overline{BHE}$ LOW to Write End	40		ns
t_{SD}	Data Set-up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[11, 12]		20	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[11]	10		ns

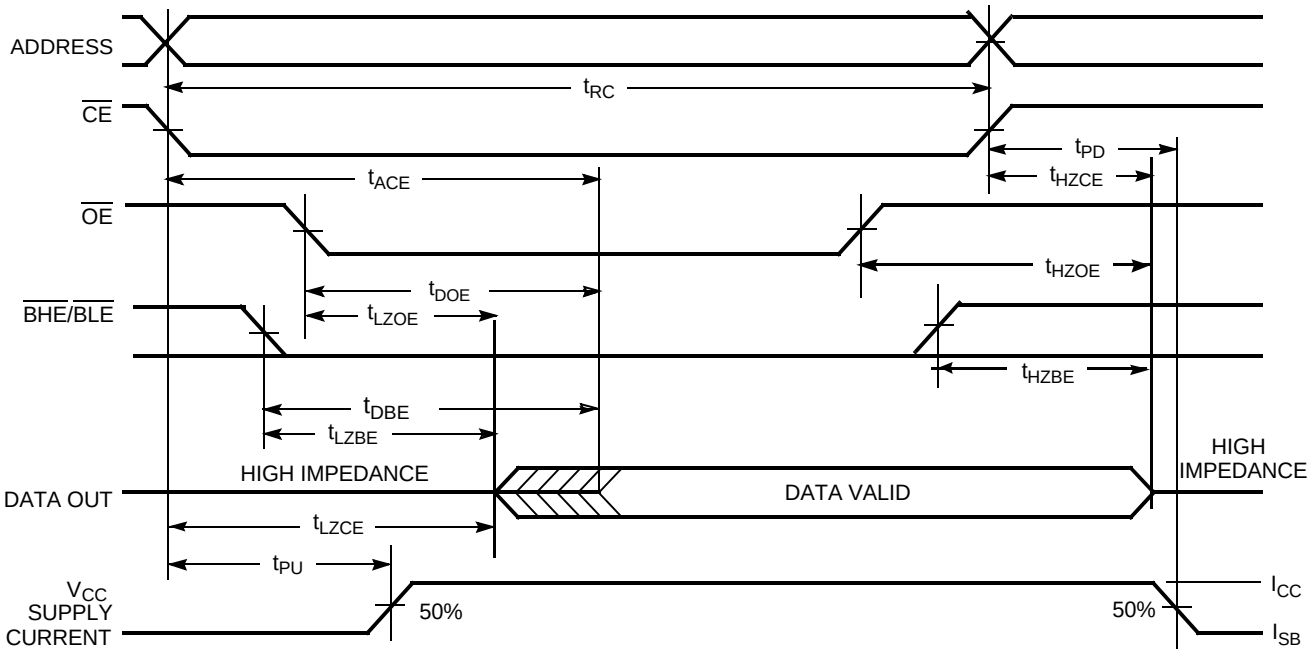
Notes:
10. Test conditions assume signal transition time of 1V/ns or less, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}.
11. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}.
12. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
13. The internal Write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

Read Cycle No. 1 (Address Transition Controlled)[14, 15]



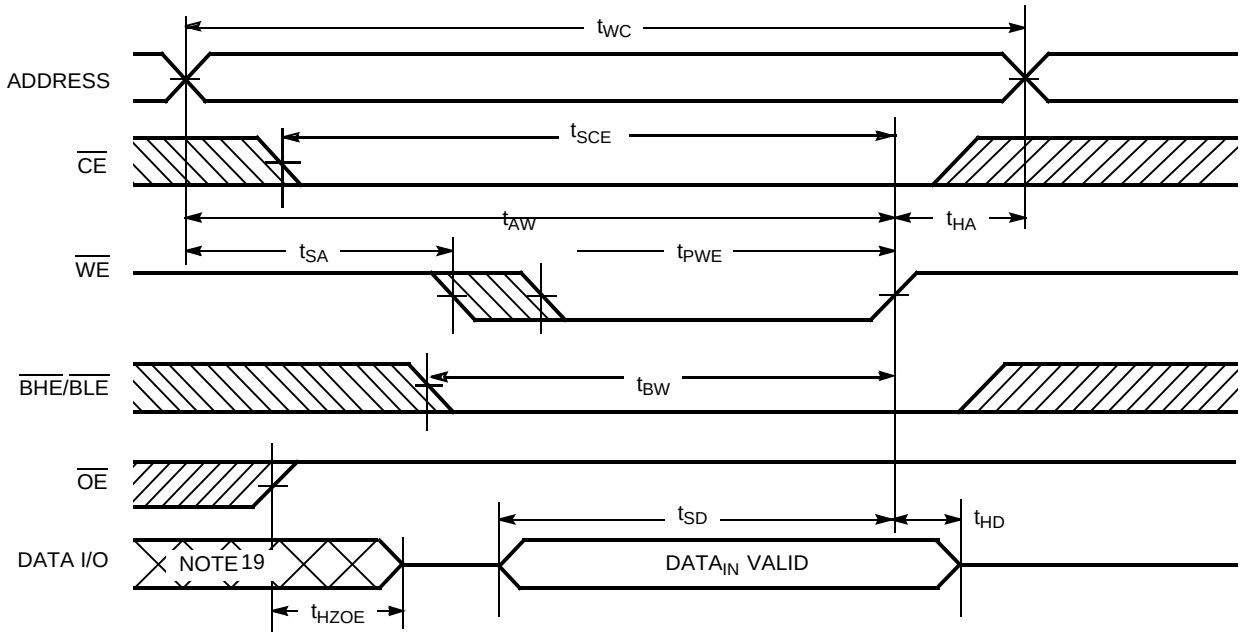
Read Cycle No. 2 ($\overline{OE}$ Controlled)[15, 16]



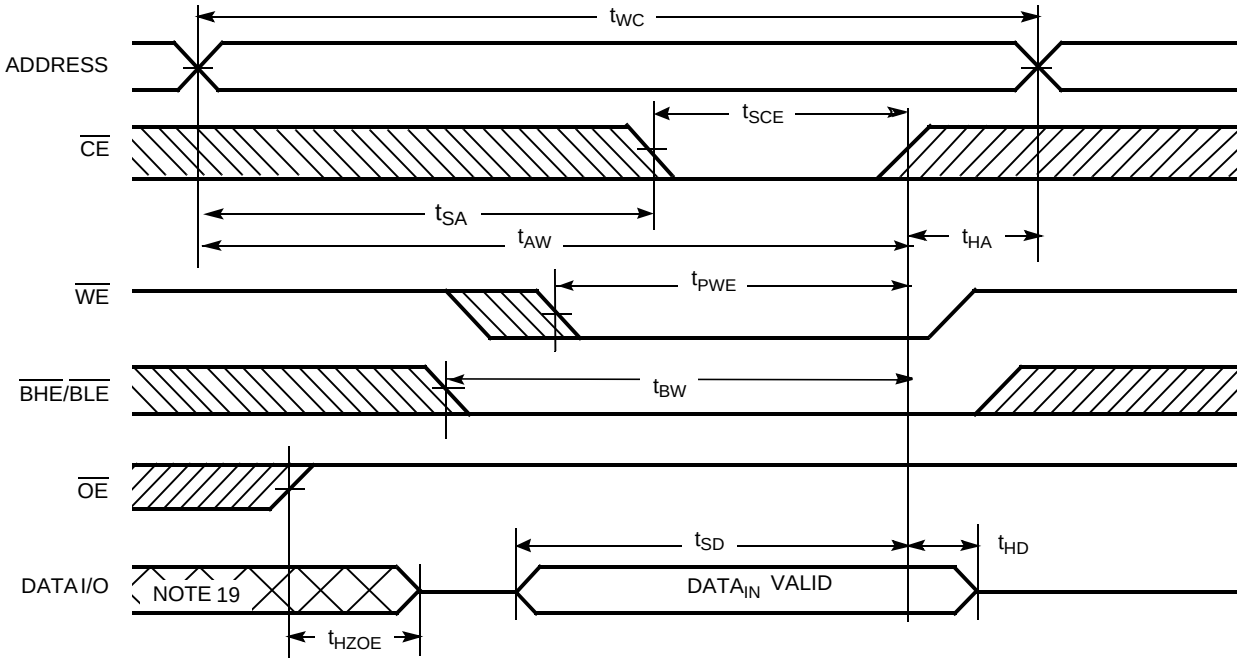
Notes:
14. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ = V_{IL}.
15. $\overline{WE}$ is HIGH for Read cycle.
16. Address valid prior to or coincident with $\overline{CE}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms(continued)

Write Cycle No. 1 (WE Controlled)[12, 13, 16, 17, 18]



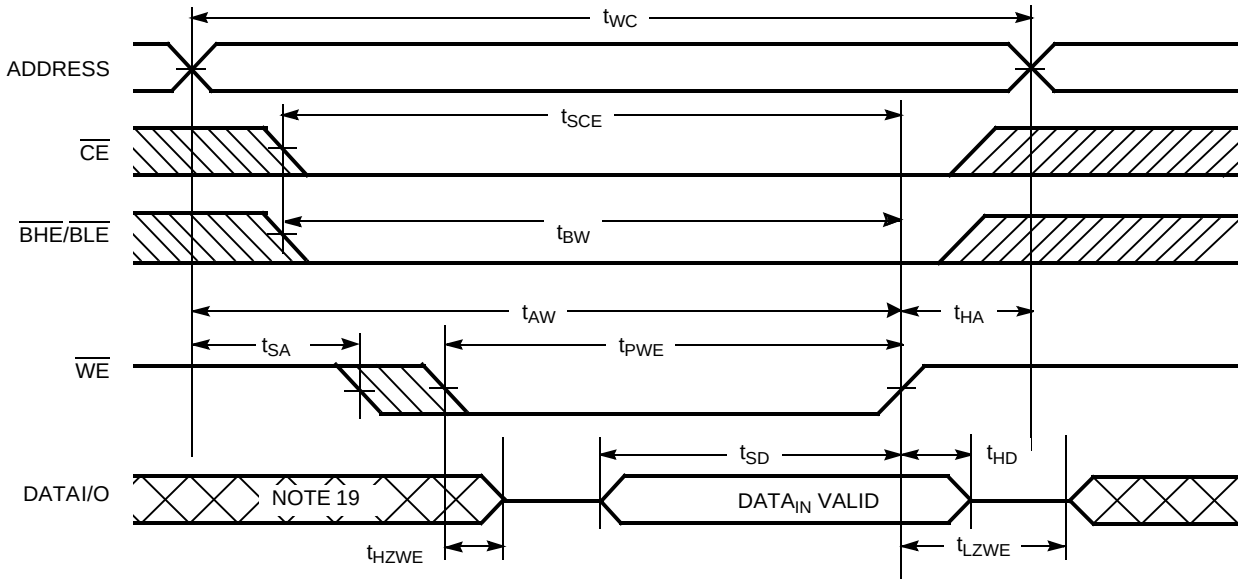
Write Cycle No. 2 (CE Controlled)[12, 13, 16, 17, 18]



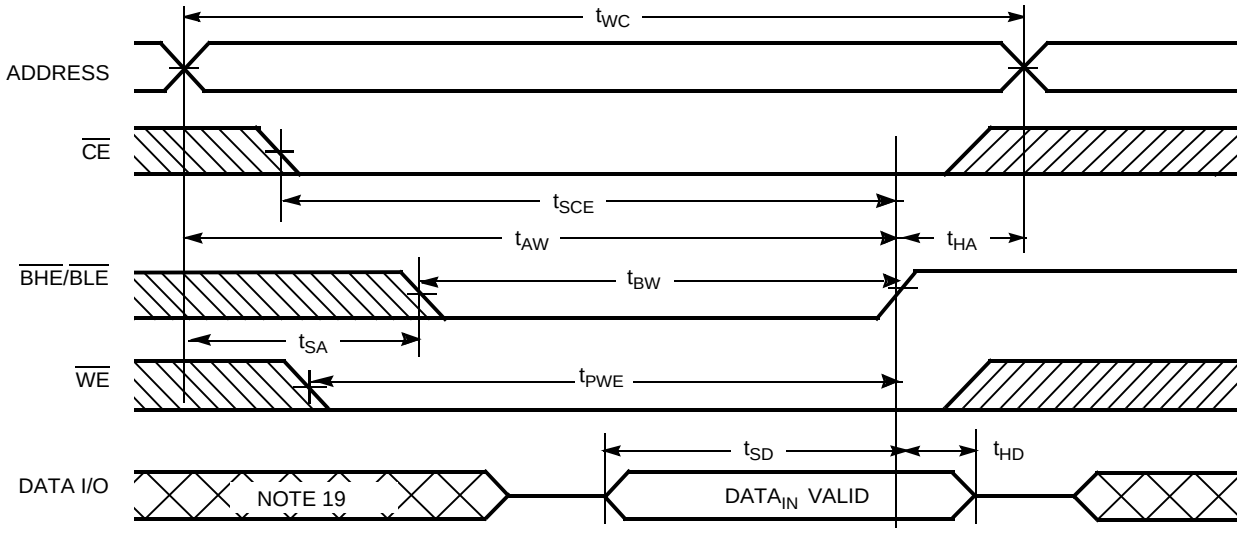
Notes:
17. Data I/O is high-impedance if $\overline{OE}$ = V_{IH}.
18. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.
19. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms(continued)

Write Cycle No. 3 (WE Controlled, OE LOW)[17, 18]



Write Cycle No. 4 (BHE/BLE-controlled, OE LOW)[17, 18]



Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	X	X	H	H	High Z	Output Disabled	Active (I_{CC})
L	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	High Z (I/O_8–I/O_{15}); Data Out (I/O_0–I/O_7)	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); High Z (I/O_0–I/O_7)	Read	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	High Z (I/O_8–I/O_{15}); Data In (I/O_0–I/O_7)	Write	Active (I_{CC})
L	L	X	L	H	Data in (I/O_8–I/O_{15}); High Z (I/O_0–I/O_7)	Write	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})

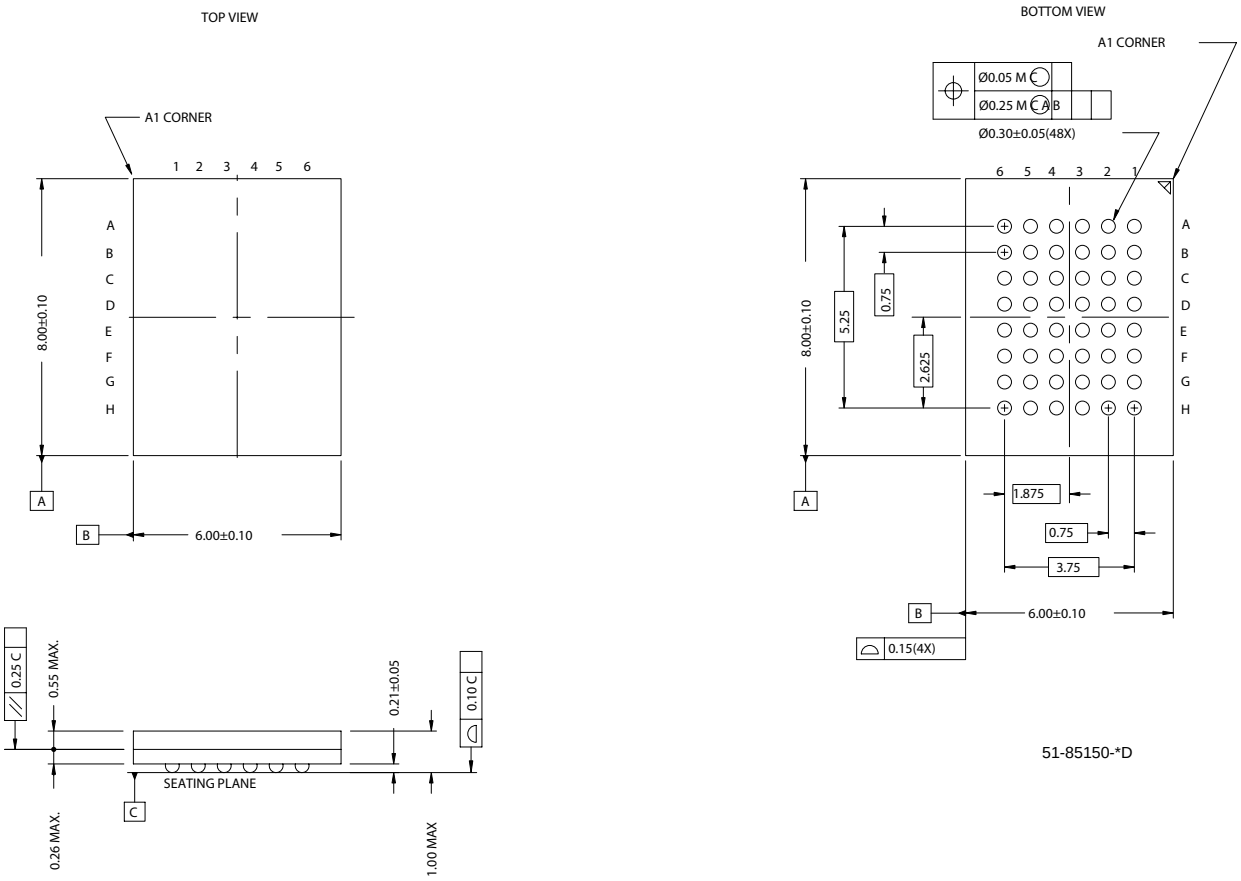
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
55	CY62126DV30LL-55BVI	51-85150	48-ball Fine-Pitch Ball Grid Array (6 x 8 x 1 mm)	Industrial
	CY62126DV30LL-55BVXI		48-ball Fine-Pitch Ball Grid Array (6 x 8 x 1 mm) (Pb-free)	
	CY62126DV30LL-55ZI	51-85087	44-pin TSOP II	
	CY62126DV30LL-55ZXI		44-pin TSOP II (Pb-free)	
	CY62126DV30L-55BVXE	51-85150	48-ball Fine-Pitch Ball Grid Array (6 x 8 x 1 mm) (Pb-free)	Automotive
	CY62126DV30L-55ZSXE	51-85087	44-pin TSOP II (Pb-free)	

Please contact your local Cypress sales representative for availability of these parts

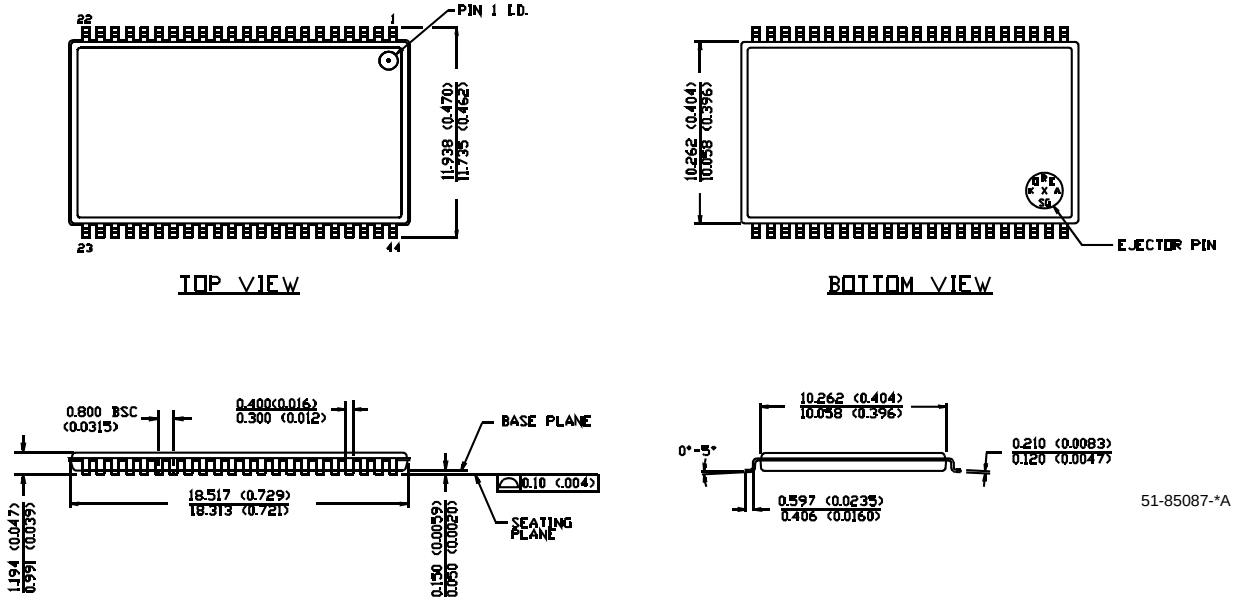
Package Diagrams

48-ball VFBGA (6 x 8 x 1 mm) (51-85150)



Package Diagrams(continued)

44-pin TSOP II (51-85087)



Document History Page

Document Title: CY62126DV30 MoBL® 1-Mbit (64K x 16) Static RAM Document Number: 38-05230				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	117689	08/27/02	JUI	New Data Sheet
*A	127313	06/13/03	MPR	Changed From Advanced Status to Preliminary. Changed I_{SB2} to 5 µA (L), 4 µA (LL) Changed I_{CCDR} to 4 µA (L), 3 µA (LL) Changed C_{IN} from 6 pF to 8 pF
*B	128340	07/22/03	JUI	Changed from Preliminary to Final Add 70-ns speed, updated ordering information
*C	129002	08/29/03	CDY	Changed I_{CC} 1 MHz typ from 0.5 mA to 0.85 mA
*D	238050	See ECN	AJU	Fixed typo: Changed t_{DBE} from 70 ns to 35 ns
*E	316039	See ECN	PCI	Added 45-ns Speed Bin in AC, DC and Ordering Information tables Added Footnote #8 on page #4 Added Pb-free package ordering information on page # 9 Changed 44-pin TSOP-II package name from Z44 to ZS44
*F	335861	See ECN	SYT	Added Temperature Ranges in the Features Section on Page # 1 Added Automotive Product Information for CY62126DV30-L for 55 ns Added I_{SB1} and I_{SB2} values for Automotive range of CY62126DV30-L for 55 ns Added Automotive Information for I_{CCDR} in the Data Retention Characteristics table Added Pb-free packages in the ordering information Changed 44-pin TSOP-II package name from ZS44 to Z44
*G	357256	See ECN	PCI	Added Pin Configuration and Package Diagram for 56-Lead QFN Package Updated Thermal Characteristics and Ordering Information Table Added Automotive Specs for I_{IX} and I_{OZ} in the DC Electrical Characteristics table on Page# 4
*H	486789	See ECN	VKN	Changed the address of Cypress Semiconductor Corporation on Page #1 from “3901 North First Street” to “198 Champion Court” Removed 45 ns and 70ns Speed bin from Product offering Removed 56-pin QFN package Updated Ordering Information Table